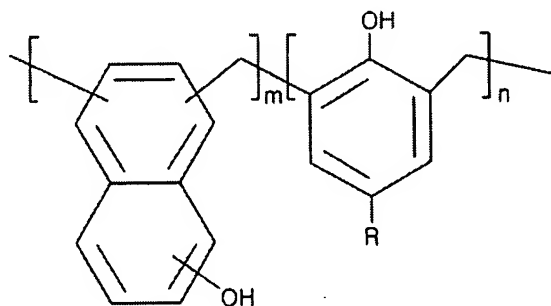


COMPOSITION FOR A BOTTOM-LAYER RESIST

ABSTRACT OF THE DISCLOSURE

A composition for a bottom-layer resist, having superior anti-
5 refractivity and dry-etch resistance for use in a bi-layer resist process
employing a light source at a wavelength of 193nm or below, is disclosed.
The composition for the bottom-layer resist contains a polymer
represented by formula 1:

<Formula 1>



10 In formula 1, R is hydrogen or a methyl group, $m/(m+n)$ is about 0.5 to about 1.0 and $n/(m+n)$ is 0 to about 0.5.